TOSHIBA TLP701

Preliminary

TOSHIBA Photocoupler GaAlAs IRED + Photo IC

TLP701

INDUSTRIAL INVERTERS INVERTER FOR AIR CONDITIONERS IGBT/POWER MOS FET GATE DRIVE

The TOSHIBA TLP701 consists of a GaAlAs light-emitting diode and an integrated photodetector.

This unit is 6-lead SDIP package. The TLP701 is 50% smaller than the 8-PIN DIP and meets the reinforced insulation class requirements of international safety standards. Therefore the mounting area can be reduced in equipment requiring safety standard certification.

The TLP701 is suitable for gate driving circuits for IGBTs or power MOSFETs. In particular, the TLP701 is capable of "direct" gate driving of low-power IGBTs.

Peak output current : ±0.6 A (max)
 Guaranteed performance over temperature : -40 to 100°C
 Supply current : 2 mA (max)
 Power supply voltage : 10 to 30 V
 Threshold input current : I_{FLH} = 5 mA (r

Threshold input current
 Switching time (t_{pLH} / t_{pHL})
 Common mode transient immunity
 I_{FLH} = 5 mA (max)
 700 ns (max)
 ±10 kV/µs (min)
 Isolation voltage
 5000 Vrms (min)

Construction mechanical rating

	7.62-mm pitch standard type	10.16-mm pitch TLPXXXF type
Creepage Distance Clearance Insulation Thickness	7.0 mm (min) 7.0 mm (min) 0.4 mm (min)	8.0 mm (min) 8.0 mm (min) 0.4 mm (min)

• UL Recognized : UL1577, File No. E67349

• Option (D4)

TÜV approved : EN60747-5-2

Certificate No. R50033433

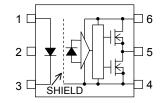
Maximum operating insulation voltage : 890 Vpk Highest permissible over voltage : 8000 Vpk

(Note) When a EN60747-5-2 approved type is needed, please designate the "Option(D4)"

Truth Table

Input	LED	Tr1	Tr2	Output
Н	ON	ON	OFF	Н
L	OFF	OFF	ON	L

Pin Configuration (Top View)



1: ANODE

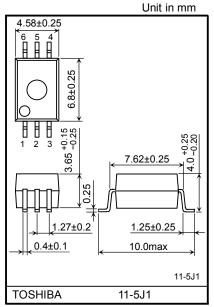
2: NC

3: CATHODE

4: GND

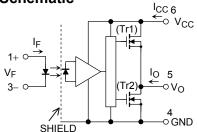
5: V_O (OUTPUT)

6: V_{CC}



Weight: 0.26 g (typ.)





A 0.1- μ F bypass capacitor must be connected between pins 6 and 4. (See Note 6.)

Maximum Ratings (Ta = 25 °C)

Characteristics		Symbol	Rating	Unit	
	Forward current		l _F	20	mA
	Forward current derating (Ta ≥ 85°C)		ΔΙ _Γ /ΔΤα	-0.54	mA/°C
LED	Peak transient forward current	(Note 1)	I _{FP}	1	А
	Reverse voltage		V _R	5	V
	Junction temperature		Tj	125	°C
	"H" peak output current	(Note 2)	I _{OPH}	-0.6	Α
or	"L" peak output current Output voltage		I _{OPL}	0.6	А
etect			Vo	35	V
Ď	Supply voltage		V _{CC}	35	V
	Junction temperature		Tj	125	°C
Oper	rating frequency	(Note 3)	f	25	kHz
Operating temperature range			T _{opr}	-40 to 100	°C
Storage temperature range		T _{stg}	-55 to 125	°C	
Lead soldering temperature (10 s) (Note 4)		T _{sol}	260	°C	
Isola	tion voltage (AC, 1 minute, R.H. ≤ 60%)	(Note 5)	BVS	5000	Vrms

Note 1: Pulse width $P_W \le 1 \mu s$, 300 pps

Note 2: Exponential waveform pulse width $P_W \le 2 \mu s$, $f \le 15 \text{ kHz}$

Note 3: Exponential waveform $I_{OPH} \le -0.3 \text{ A} (\le 2 \mu \text{s}), I_{OPL} \le +0.3 \text{ A} (\le 2 \mu \text{s}), Ta = 100 ^{\circ}\text{C}$

Note 4: For the effective lead soldering area

Note 5: Device considered a two-terminal device: pins 1, 2 and 3 paired with pins 4, 5 and 6 respectively.

Note 6: A ceramic capacitor $(0.1 \, \mu F)$ should be connected from pin 6 to pin 4 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching property. The total lead length between capacitor and coupler should not exceed 1 cm.

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Recommended Operating Conditions

Characteristics		Symbol	Min	Тур.	Max	Unit
Input current, ON	(Note 7)	I _{F (ON)}	7.5		10	mA
Input voltage, OFF		V _F (OFF)	0	-	0.8	V
Supply voltage		V _{CC}	10	_	30	V
Peak output current		I _{OPH} / I _{OPL}	_	_	± 0.2	Α
Operating temperature		T _{opr}	-40	_	100	°C

Note 7: Input signal rise time (fall time) $< 0.5 \ \mu s.$

Electrical Characteristics (Ta = -40 to 100 °C, unless otherwise specified)

Characteristics		Symbol	Test Circuit	Test Condition		Min	Typ.*	Max	Unit
Forward voltage		V _F	_	$I_F = 5$ mA, $Ta = 25$ °C		_	1.55	1.70	V
Temperature coefficient of forward voltage		ΔV _F /ΔTa	_	I _F = 5 mA	I _F = 5 mA		-2.0	_	mV/°C
Input reverse current		I _R	_	V _R = 5 V, Ta = 25	°C	_	_	10	μА
Input capacitance		C _T	_	V =0 V, f = 1 MHz	, Ta = 25 °C		45	_	pF
	"H" Level	I _{OPH1}	1	V _{CC} = 15 V	V ₆₋₅ = 4 V	-0.2	-0.38	_	
Output current	п Levei	I _{OPH2}	1 1	V ₆₋₅ = 10 V	-0.4	-0.60	_	1	
(Note 8)	"L" Level	I _{OPL1}	2	V _{CC} = 15 V	V ₅₋₄ = 2 V	0.2	0.36	_	- A
	L Level	I _{OPL2}		$I_F = 0 \text{ mA}$	V ₅₋₄ = 10 V	0.4	0.62	_	
	"H" Level	V _{OH}	3	V _{CC} = 10 V	$I_O = -100 \text{ mA},$ $I_F = 5 \text{ mA}$	6.0	8.5	_	· V
Output voltage	"L" Level	V _{OL}	4		$I_O = 100 \text{ mA},$ $V_F = 0.8 \text{ V}$	_	0.4	1.0	
Cupply ourrant	"H" Level	I _{CCH}	5	V _{CC} = 10 to 30 V	I _F = 10 mA	_	1.4	2.0	mA
Supply current	"L" Level	I _{CCL}	6	V _O =Open	I _F = 0 mA	_	1.3	2.0	
Threshold input current	$L \rightarrow H$	I _{FLH}	_	V _{CC} = 15 V, V _O > 1 V		_	2.5	5	mA
Threshold input voltage	$H \rightarrow L$	V_{FHL}	_	V _{CC} = 15 V, V _O < 1 V		0.8	_	_	V
Supply voltage		V _{CC}	_	_	_	10	_	30	V

(*): All typical values are at Ta = 25°C

Note 8: Duration of lo time \leq 50 μ s, 1 pulse

Note 9: This product is more sensitive than conventional products to electrostatic discharge (ESD) owing to its low power consumption design.

It is therefore all the more necessary to observe general precautions regarding ESD when handling this component.

Isolation Characteristics (Ta = 25 °C)

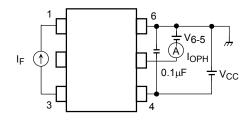
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	CS	V = 0 V , f = 1MHz (Note 5	_	1.0	_	pF
Isolation resistance	R _S	R.H. ≤ 60 %, V _S = 500 V (Note 5	1×10 ¹²	10 ¹⁴	_	Ω
Isolation voltage	BVS	AC, 1 minute	5000	_	_	Vrms
		AC, 1 second, in oil	_	10000	_	VIIIIS
		DC, 1 minute, in oil	_	10000	_	Vdc

Switching Characteristics (Ta = -40 to 100 °C, unless otherwise specified)

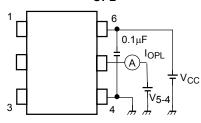
Characteristics		Symbol	Test Circuit	Test Condition		Min	Typ.*	Max	Unit	
Dana andian dalamina	$L \rightarrow H$	t _{pLH}	7	Vcc = 30 V	$I_F = 0 \rightarrow 5 \text{ mA}$	100	_	700		
Propagation delay time	$H \rightarrow L$	tpHL			$I_F = 5 \rightarrow 0 \text{ mA}$	100	_	700		
Output rise time (10-90 %	Output rise time (10–90 %) t_{Γ} $R_{g} = 47 \Omega$		$V_{CC} = 30 \text{ V}$ $R_g = 47 \Omega$ $C_g = 3 \text{ nF}$	$I_F = 0 \rightarrow 5 \text{ mA}$		50	_	ns		
Output fall time (90–10 %)		tf		C _g = 3 nF	$I_F = 5 \rightarrow 0 \text{ mA}$	_	50	_	1	
Propagation delay difference between any two parts or channels		PDD t _{pHL} -t _{pLH}			I _F = 0 , 5 mA	-500	_	500		
Common mode transient i at HIGH level output	mmunity	CMH			V _{CM} =1000 Vp-p	$I_F = 5 \text{ mA}$ $V_{O \text{ (min)}} = 26 \text{ V}$	-10000	_	_	V/μs
Common mode transient immunity at LOW level output		CML	8	V _{CC} = 30 V Ta = 25 °C	I _F = 0 mA V _{O (max)} = 1 V	10000	_		v/μs	

(*): All typical values are at Ta = 25 °C.

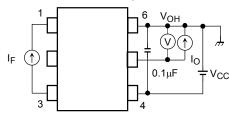
Test Circuit 1: IOPH



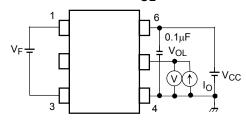
Test Circuit 2: IOPL



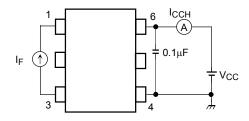
Test Circuit 3: V_{OH}



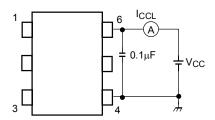
Test Circuit 4: V_{OL}



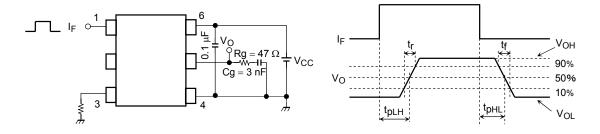
Test Circuit 5: Icch



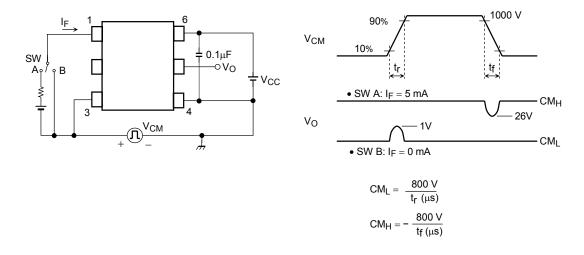
Test Circuit 6: I_{CCL}



Test Circuit 7: t_{pLH} , t_{pHL} , t_{r} , t_{f} , PDD



Test Circuit 8: CM_H, CM_L



 CM_{L} (CM_H) is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the LOW (HIGH) state.

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